EC 447 ACTIVE FILTERS COURSE PROJECT REPORT

REALIZATION OF 4TH ORDER LOW PASS FILTER USING Gm - C

Submitted by

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VII semester B.Tech ECE

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AIM

Design a Transconductance-C (Gm-C) low pass filter in $0.35~\mu m$ CMOS technology node from TSMC using LTSpice circuit simulator (or any other suitable circuit simulator) for the specifications mentioned.

BROAD EXPECTATIONS:

Realizing an ideal Gm-C Filters

- 1. a) Ideal Filer using RLC circuit which meets the specifications
 - b) Ideal Gm-C filter for the specifications using macromodel for the Gm.
- 2. Designing the transconductor in $0.35~\mu m$ CMOS technology node from TSMC and validating its use as a Gm-C integrator.

The capacitor calculated to be used in the first node of the filter may be used as the integrating capacitor for testing the Gm-C integrator.

3. Realize the transistor level Gm-C filter for the given specification.

COMMON SPECIFICATIONS:

- 1. Fourth order Maximally flat response
- 2. Power supply 3.3 V
- 3. Use length of 0.5 µm for all transistors
- 4. Use even number of fingers for the transistors.

TRANSCONDUCTOR SPECIFICATIONS:

Gm = 1 mS
 Gate overdrive for input transistors = 200 mV
 Input/output common-mode voltage = 1.65 V

FILTER SPECIFICATIONS:

Attenuation at pass band edge = 2 dB
 Band-edge = 110 MHz

METHODOLOGY:

- a. Ideal filter realization using RLC which meet the specifications.
- I. Initially fourth order prototype Butterworth filter is designed and verified using LT Spice.

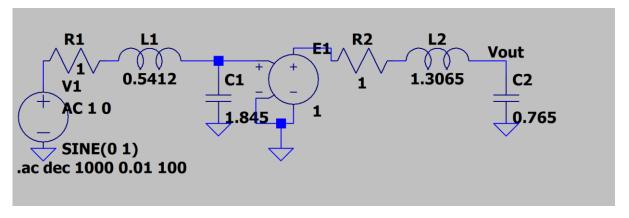
<u>Design:</u>

	A Committee of the Comm
0.	Ideal Filter using RLC circuit
	Given: pass bend attenuation = 2 dB = 110 Mz Band edge = 4. order, n = 4. wp = 110 Mx 21T , pass band edge for maximally flat response wp = 4.
•	wp,b -> pano band edge for butterworth filter.
	-> Finding the value of 6
	- 20 log / To(yw) = 2
	$\Rightarrow -20\log\left(\frac{1}{\sqrt{1+e^2}}\right) = 2$
•	$=) 1+6^{2} = 10^{\circ \cdot 2}$ $=) [6 = 0.7647]$
,	$Q_1 = \frac{1}{2 \cos(22.5)} = 0.5411$
	Q2 = 1 = 1.3065 2105 (67.5)
	-> Transfer franction of a 4th order prototype Butterwith fitter=
	$(s^2 + \frac{1}{Q_1}s + 1)(s^2 + \frac{1}{Q_2}s + 1)$

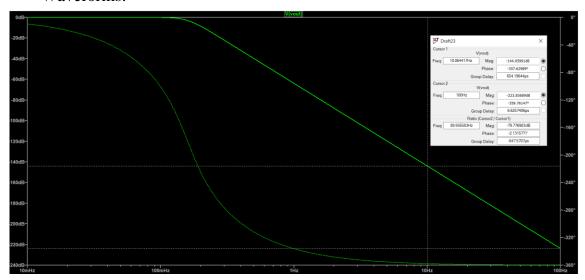
For any pass band edge $w_{p,B}$. $ Tn(jw) ^2 = \frac{1}{1+6^2w^{2n}}$ For any pass band edge $w_{p,B}$. $ Tn(jw) ^2 = \frac{1}{1+w^{2n}}$ For any pass band edge $w_{p,B}$. $ Tn(jw) _{wpmf} = Tn(jw) _{wpmg}$ $ w_{p,mf} ^{2n} e^2 = \left(\frac{w}{w_{p,mf}}\right)^{2n}$ $ w_{p,mf} ^{2n} e^2 = \left(\frac{w}{w_{p,mf}}\right)^{2n} e^2 = $
For maximally flat suppore fills $ T_{n(j\omega)} ^{2} = \frac{1}{1+e^{2\omega^{2n}}}$ For any pass band edge $w_{p,B}$. $ T_{n(j\omega)} ^{2} = \frac{1}{1+\omega^{2n}}$ For any pass band edge $w_{p,B}$. $ T_{n(j\omega)} _{upmt} = T_{n(j\omega)} _{upmt}$ $= T_{n(j\omega)} _{upmt$
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For butterwith, $ Tn(j\omega) ^{2} = \frac{1}{1+\omega^{2}n}$ For any pass band edge $w_{p,B}$, $ Tn(j\omega) _{upmt} = Tn(j\omega) _{up,B}$ $(-\omega)_{p,mt}^{2n} \in \mathcal{L} = (-\omega)_{p,Bp}^{2n}$
For any pass band edge $w_{p,B}$, $ Tn(j\omega) _{\omega pmf} = Tn(j\omega) _{\omega pmf}$ $= \frac{ Tn(j\omega) _{\omega pmf}}{ \omega_{p,mf} ^{2n}} e^{2} = \frac{ \omega _{\omega p,BP}}{ \omega_{p,BP} ^{2n}}$ $\Rightarrow w_{p,B} = e^{-1/n} w_{p,mf} \Rightarrow w_{p,B} = (0.7647)^{-0.25} \times (10\times10^{6}\times271)$
For any pair band edge $w_{p,B}$,
For any pass band edge $w_{p,B}$, $ Tn(j\omega) _{\omega pmf} = Tn(j\omega) _{\omega pmf}$ $= \frac{ Tn(j\omega) _{\omega pmf}}{ \omega_{p,mf} ^{2n}} e^{2} = \frac{ \omega _{\omega p,BP}}{ \omega_{p,BP} ^{2n}}$ $\Rightarrow w_{p,B} = e^{-1/n} w_{p,mf} \Rightarrow w_{p,B} = (0.7647)^{-0.25} \times (10\times10^{6}\times271)$
$ Tn(j\omega) _{wpmf} = Tn(j\omega) _{wpjB}$ $\left(\frac{\omega}{w_{p,mf}}\right)^{2n} \epsilon^{2} = \left(\frac{\omega}{w_{pjBP}}\right)^{2n}$ $\Rightarrow w_{pjB} \epsilon^{-1/n} w_{p,mf} \Rightarrow w_{pjB} \epsilon^{-1/n} w_{p,mf} \Rightarrow w_{pjB} \epsilon^{-1/n} w_{p,mf} = w_{pjB} \epsilon^{-1/n} w_{pjB} = w_{pjB} = w_{pjB} \epsilon^{-1/n} w_{pjB} = w_{pjB} = w_{pjB} = w_$
$\frac{(\omega)^{2n} \epsilon^2}{(\omega_{p,mf})^{2n} \epsilon^2} = \frac{(\omega)^{2n}}{(\omega_{p,gp})^{2n}}$ $\Rightarrow (\omega_{p,g} \epsilon^{-1/n} \omega_{p,mf}) \Rightarrow (\omega_{p,g} \epsilon^{-1/n} \omega_{p,mf}) = (\omega_{p,g} \epsilon^{-1/n} \omega_{p,g}) = (\omega_{p,g} \epsilon^{-1/n} \omega_{p,g})$
$\frac{(\omega)^{2n} \epsilon^2}{(\omega_{p,mf})^{2n} \epsilon^2} = \frac{(\omega)^{2n}}{(\omega_{p,gp})^{2n}}$ $\Rightarrow (\omega_{p,g} \epsilon^{-1/n} \omega_{p,mf}) \Rightarrow (\omega_{p,g} \epsilon^{-1/n} \omega_{p,mf}) = (\omega_{p,g} \epsilon^{-1/n} \omega_{p,g}) = (\omega_{p,g} \epsilon^{-1/n} \omega_{p,g})$
⇒ ω _{P,B} : ε- ¹ /n ω _{P,M} f ⇒ ω _{P,B} : (0.7647) × (110×106×2π)
=> Wp.B: E-1/n wp,mf => Wp.B= (0.7647) x (110×106×277) = 739.095 M rad/se
= 739.095 M rad/se
. Sie is in tall le
-> Finding the values of Li, Ci, Lz, Cz.
$R_1 = R_2 = 1 \text{ K} \Omega$
71272172
$Q_1 = \frac{1}{R_1} \sqrt{\frac{L_1}{C_1}} - 0 \text{ and } w_p = \frac{1}{\sqrt{\frac{L_1}{C_1}}} - 0$
NIVCI VLICI
Multiplying 1 and 10
$\Rightarrow Q_1 w_{P,b} = \frac{1}{R_1 C_1} \Rightarrow C_1 = \frac{1}{Q_1 w_{P,b} R_1}$
0.541× 739.095×106×103 = 2.5pF

L1 = 012 R12C1		
$= (0.541)^2 \times (10^3)^2 \times (10^3)$	2.5 ×10 -12	
4 = 0.731µH		
-		
Similarly,		
U		
C2 = 1		
de about		
= 1.3065 x 739.09	15 ×10 6 ×10 3	
	3 110 210	
= 1.0355pF		
L2 = 1.0355 x10-12 x	(1.3065)2x(103)2	
= 1.76744		
" R1 = 1K92	R2 = 1k.M	_lnà- -
L1 = 0.73/44	L2 = 1.767,4H	1/
C1 = 2.5pF	C2 = 1.0355pf	
the set of the last		

Circuit: (Prototype)

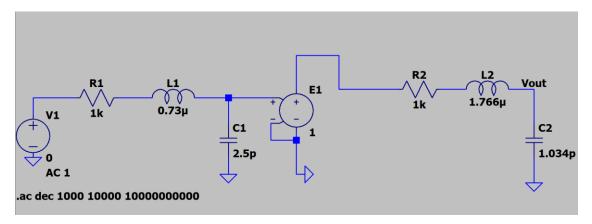


Waveforms:

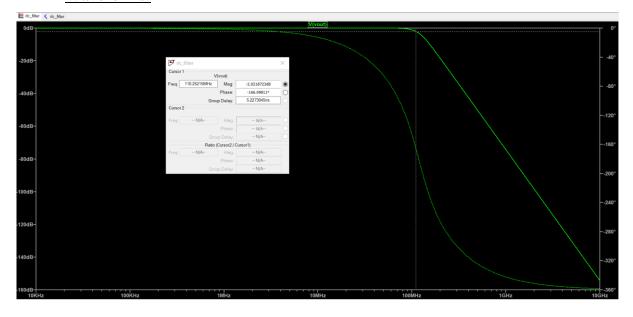


- II. For the given Maximally flat response, corresponding Butterworth pass band edge has been found out.
- III. Using the new butterworth pass band edge and given transconductance Gm=1mS, R1, L1, C1 and R2, C2, L2 are calculated.

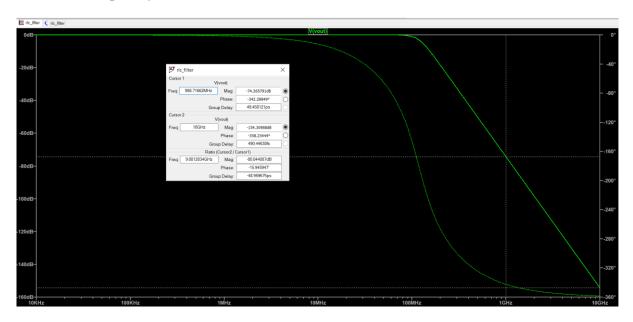
 <u>Circuit:</u>



Waveforms:



From the graph,
At frequency 110 MHz, Gain obtained = **-2.02dB** (Attenuation=2 dB)

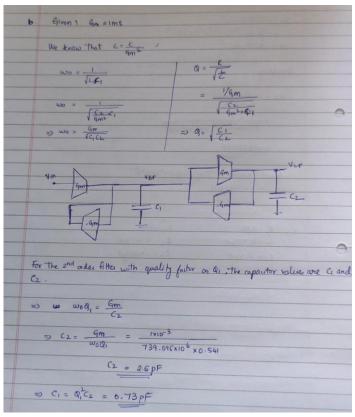


From the Graph,

Roll-off obtained at wp=110MHz is **-80.044087** which is equal to the roll-off of a 4^{th} butterworth response -20x4 = -80

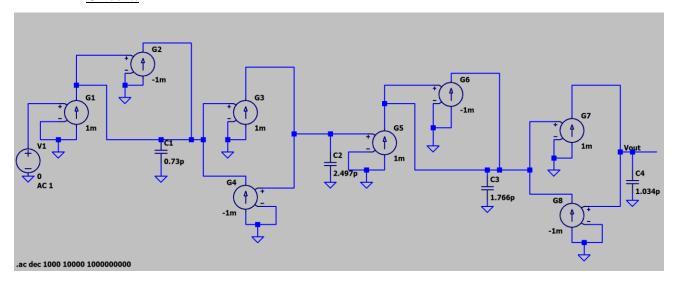
- b) Ideal Gm-C filter for the specifications using macromodel for the Gm.
- I. As 4th order Butterworth Low Pass Filter is obtained by cascading 2 second order low pass filters, each 2nd low pass filter is obtained using Gm and C and are cascaded directly without any buffer as there is no loading effect.

Design:

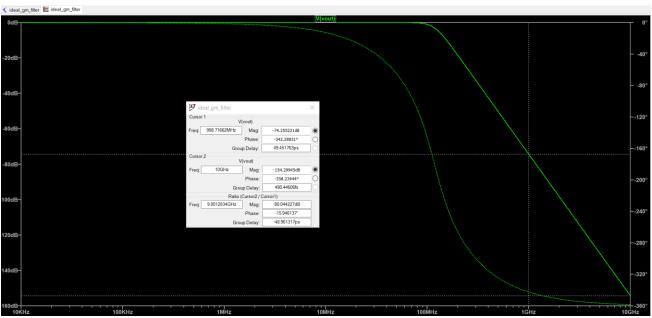


Fox the 2nd order of the with Quality factor as Q2, the capacitor values are
Cz and C4.
·· O Gm
$= \frac{Gm}{C4}$
$=)$ $C_4 = \frac{1 \times 10^{-3}}{10^{-3}}$
739.095 x10 6 X @ 1.3065
=1.035pF
$= C_3 = Q_2^2 C_4$ $= (1.3065)^2 \times 1.035 \times 10^{-12}$
= 1.767pF
.: C1= 0.73pf C3= 1.767pF
C2 = 2.5pF

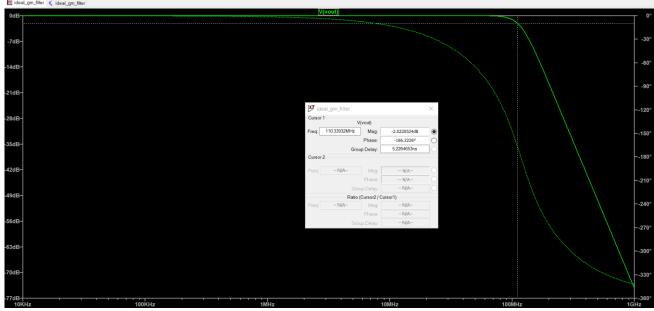
Circuit:



Waveforms:



From the graph,
Gain at wp=110MHz is -2.0220524dB (Attenuation=2dB approximately)



From the graph,

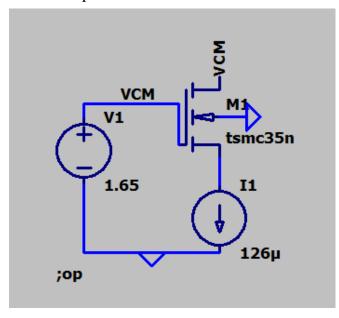
Roll-off measured in between 1GHz and 10GHz is -80.0442 which is equal to the roll-off of a 4^{th} butterworth response -20x4= -80dB.

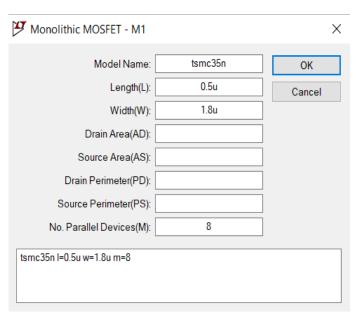
2. Designing the transconductor in 0.35 μm CMOS technology node from TSMC and validating its use as a Gm-C integrator.

Transconductance = 1 mS

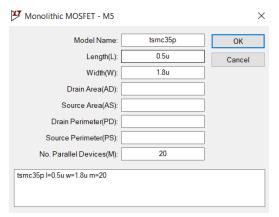
Vds,sat = 200 mV

NMOS Specifications tuned:

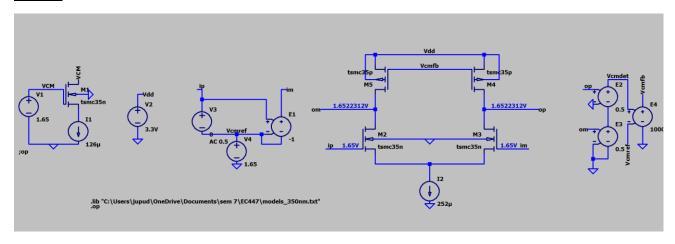




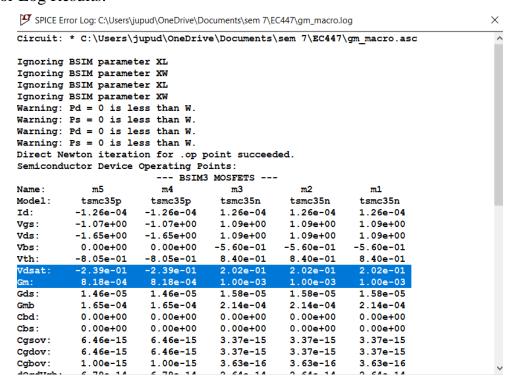
PMOS specifications obtained:



Circuit:

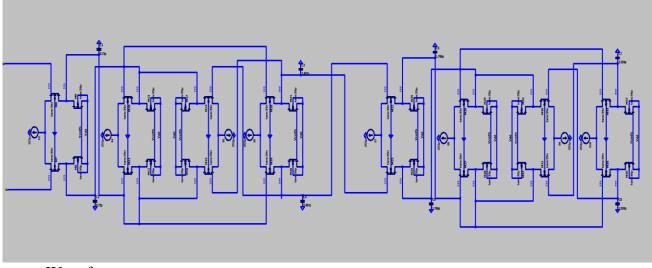


SPICE Error Log Results:



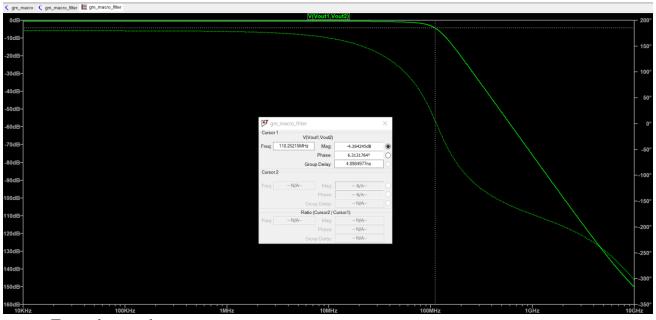
Required values of Vdsat and Gm are obtained by tuning W, number of fingers and Current value in the current source and the functioning of Gm-C integrator is verified.

3. 4th-order Low Pass Butterworth Filter realization using Gm implemented in the previous step: Circuit:



Waveforms:

The input given is differential input, so the differential voltage is measured across the output.



From the graph,

Gain obtained at pass band edge=-4.264245dB.

DC Gain obtained=-565.58289mdB.

There is a slight deviation than the required gain which is due to non-idealities like parasitic capacitances and output resistances of all the transconductors.
